



DSS3515M

15V PNP LOW SATURATION TRANSISTOR IN X1-DFN1006-3

Features

- BVcEo > -15V
- Ic = -500mA High Collector Current
- Icm = -1A Peak Pulse Current
- P_D = 1000mW Power Dissipation
- Low Collector-Emitter Saturation Voltage, VCE(sat)
- 0.60mm² Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type DIODES™ DSS2515M
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

 An automotive-compliant part is available under separate datasheet (DSS3515MQ)

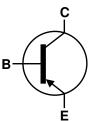
Mechanical Data

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

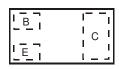
X1-DFN1006-3



Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 4)

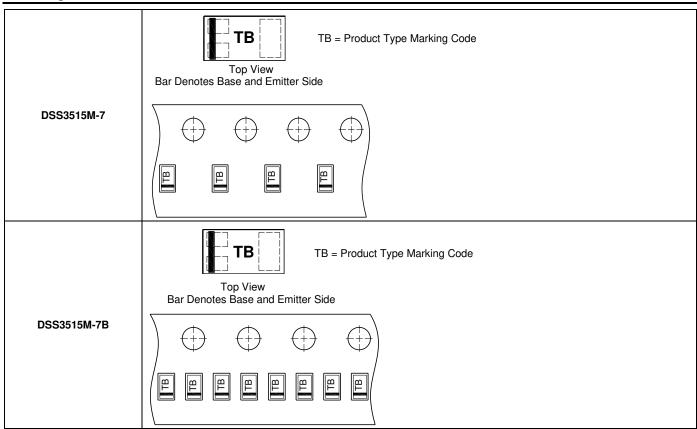
Part Number	Dookogo	Moulsing	Reel Size (inches)	Tape Width (mm)	Packing		
Part Number	Package	Marking	neer Size (Inches)	rape widin (ililii)	Qty.	Carrier	
DSS3515M-7	X1-DFN1006-3	TB	7	8	3,000	Reel	
DSS3515M-7B	X1-DFN1006-3	TB	7	8	10,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information





Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VcBO	-15	V
Collector-Emitter Voltage	VCEO	-15	V
Emitter-Base Voltage	VEBO	-6	V
Collector Current - Continuous	Ic	-500	mA
Peak Pulse Collector Current	Ісм	-1	Α
Peak Base Current	Івм	-100	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Dower Dissipation	(Note 5)	400		mW	
Power Dissipation	(Note 6)	- P _D	1000	IIIVV	
Thermal Decistores, Junction to Ambient	(Note 5)	D	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	- Reja	120	- G/VV	
Thermal Resistance, Junction to Lead (Note 7)		R _{θJL}	120	°C/W	
Operating and Storage and Temperature Ran	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

^{5.} For the device mounted on minimum recommended pad layout 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition.

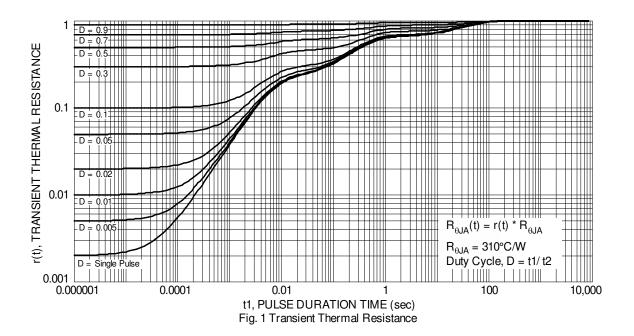
^{6.} Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

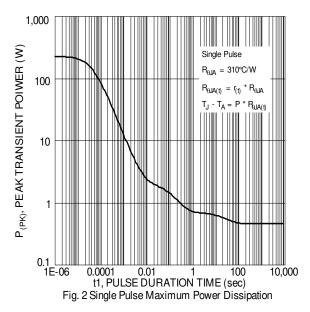
7. Thermal resistance from junction to solder-point (on the exposed collector pad).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	ВУсво	-15	_	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	-15	_	_	V	Ic = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6	_	_	V	$I_E = -100 \mu A$, $I_C = 0$
Collector Cutoff Current	I _{CBO}	_		-100 -50	nA μA	V _{CB} = -15V, I _E = 0 V _{CB} = -15V, I _E = 0, T _A = +150°C
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	V _{EB} = -5V, I _C = 0
ON CHARACTERISTICS (Note 9)						
DC Current Gain	hFE	200 150 90			_	V _{CE} = -2V, I _C = -10mA V _{CE} = -2V, I _C = -100mA V _{CE} = -2V, I _C = -500mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-25 -150 -250	mV	Ic = -10mA, I _B = -0.5mA Ic = -200mA, I _B = -10mA I _C = -500mA, I _B = -50mA
Collector-Emitter Saturation Resistance	RCE(sat)	_	_	500	mΩ	Ic = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-1.1	V	I _C = -500mA, I _B = -50mA
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	-0.9	V	V _{CE} = -2V, I _C = -100mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	Cobo			10	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100	340	_	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

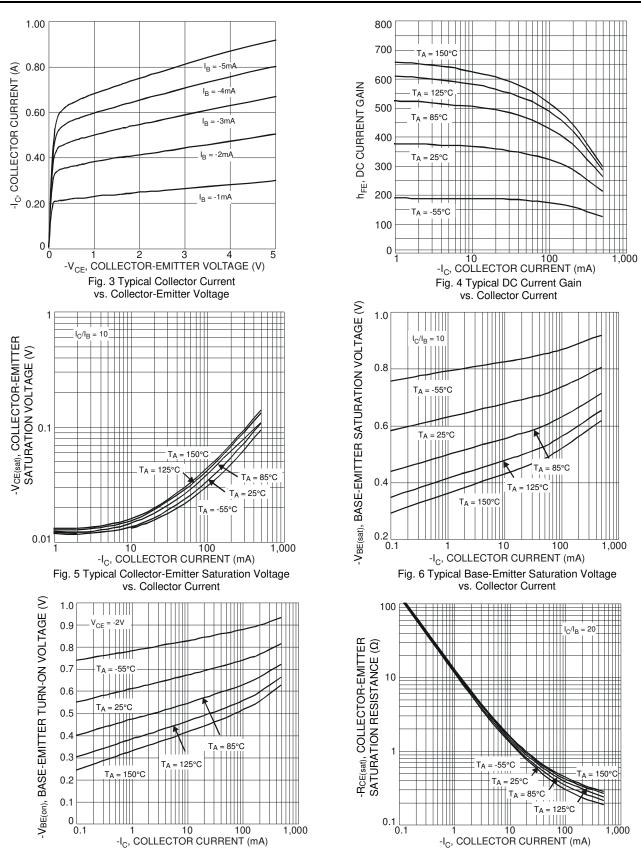


Fig. 7 Typical Base-Emitter Turn-On Voltage

vs. Collector Current

Fig. 8 Typical Collector-Emitter Saturation Resistance

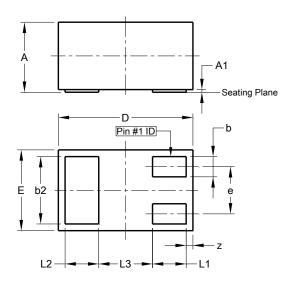
vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3

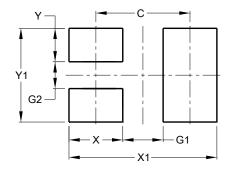


X1-DFN1006-3						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
E	0.55	0.675	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
Z	0.02	0.08	0.05			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70



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